

# 93475

## 1024 x 4-Bit Static Random Access Memory

Bipolar Division

TTL Bipolar Memory

**Description**

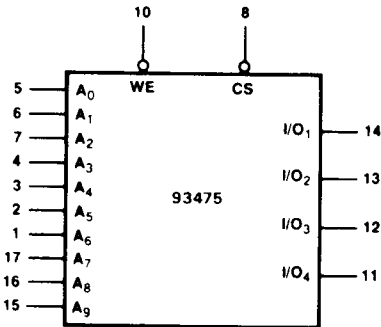
The 93475 is a 4096-bit read/write Random Access Memory (RAM), organized 1024 words by four bits per word. It is designed for high speed cache, control and buffer storage applications. The military version of the 93475 is available in two speeds, "standard" speed and an "A" grade. The device includes full on-chip decoding and an active LOW Chip Select line.

- **Address Access Time — 45 ns Max**
- **Chip Select Access Time — 35 ns Max**
- **Features Three State Outputs**
- **Common Data I/O's**
- **Industry Standard 2114 Pinout**
- **Power Dissipation — 0.16 mW/Bit Typ**
- **Power Dissipation Decreases with Increasing Temperature**

**Pin Names**

A <sub>0</sub> -A <sub>9</sub>	Address Inputs
$\overline{CS}$	Chip Select Input (Active LOW)
$\overline{WE}$	Write Enable Input (Active LOW)
I/O <sub>1</sub> -I/O <sub>4</sub>	Data Input/Data Outputs

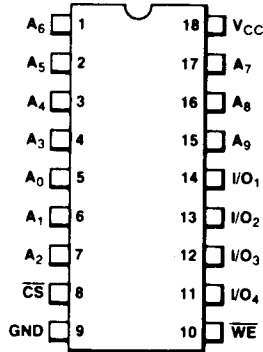
**Logic Symbol**



V<sub>CC</sub> = Pin 18  
GND = Pin 9

**Connection Diagram**

**18-Pin DIP (Top View)**

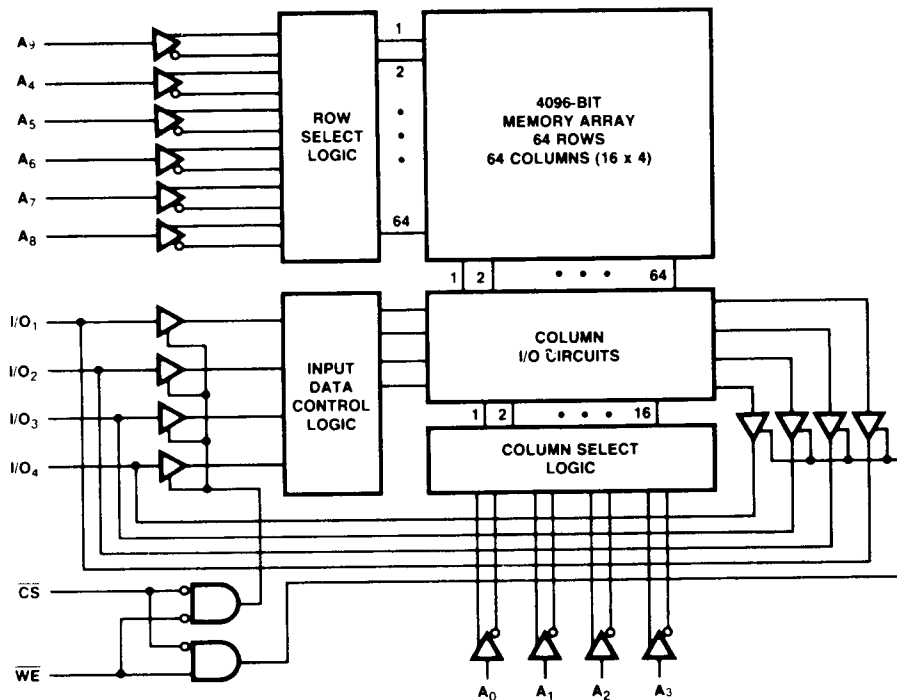


**Note:**

The 18-pin Flatpak version has the same pinout connections as the Dual In-line package.

ADVANCE INFORMATION

## Logic Diagram



## Functional Description

The 93475 is a fully decoded 4096-bit read/write Random Access Memory organized 1024 words by four bits per word. Word selection is achieved by means of a 10-bit address,  $A_0$  through  $A_9$ .

One Chip Select input is provided for logic flexibility or for memory array expansion of up to 8196 bits without the need for external decoding. For larger memories, the fast chip select access time permits the decoding of Chip Select, ( $\overline{CS}$ ) from the address without affecting system performance.

The read and write functions of the 93475 are controlled by the state of the active LOW Write Enable ( $\overline{WE}$ ) input. When  $\overline{WE}$  is held LOW and the chip is selected, the data at  $I/O_1$  through  $I/O_4$  is written into the addressed locations. Since the write function is level triggered, data must be held stable at the data input for at least  $t_{WSD(\min)}$  plus  $t_{W(\min)}$  to insure a valid write.

When  $\overline{WE}$  is held HIGH and the chip selected, data is read from the addressed location and presented at the outputs ( $I/O_1$ - $I/O_4$ ).

The 93475 has three-state outputs for use in bus organized systems.

## Truth Table

Inputs		I/O <sub>1</sub> -I/O <sub>4</sub>	Mode
$\overline{CS}$	$\overline{WE}$		
H	X	HIGH Z	Not Selected
L	H	DOUT	Read
L	L	DIN HIGH Z	Write

H = HIGH Voltage Level (2.4 V)

L = LOW Voltage Level (.5 V)

X = Don't Care (HIGH or LOW)

Fig. 1 AC Test Load Output Load

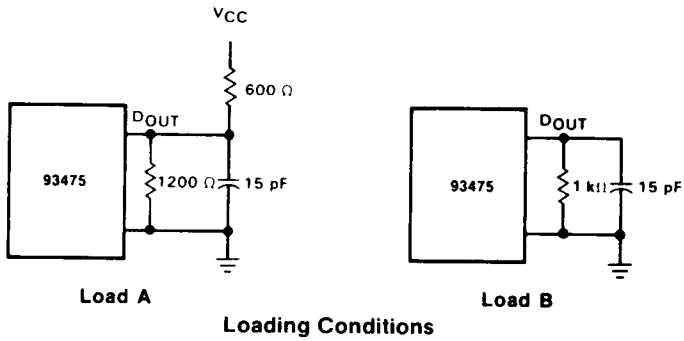
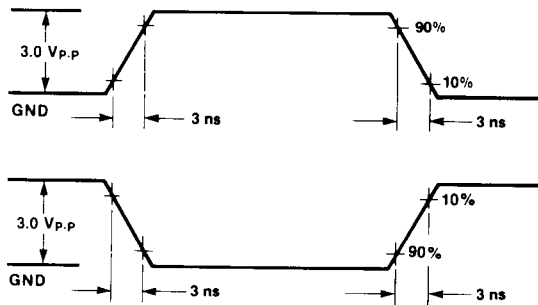


Fig. 2 Input Levels



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